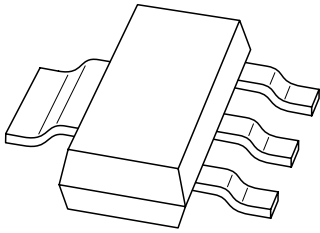


# DATA SHEET



**PZT2222A**

**NPN switching transistor**

Product data sheet  
Supersedes data of 1997 Jun 02

1999 Apr 14

# NPN switching transistor

# PZT2222A

### FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

### APPLICATIONS

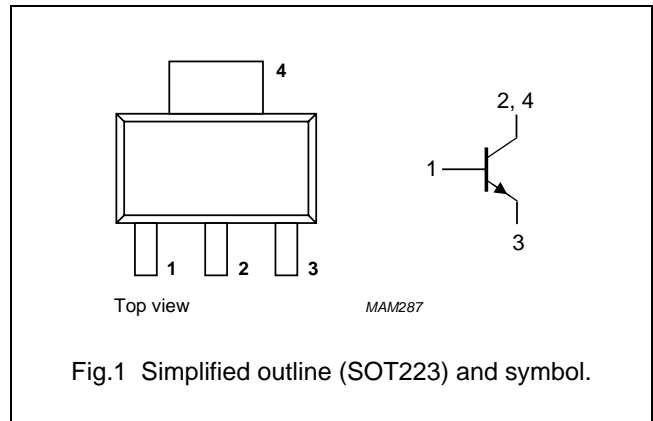
- Switching and linear amplification.

### DESCRIPTION

NPN switching transistor in a SOT223 plastic package.  
 PNP complement: PZT2907A.

### PINNING

| PIN  | DESCRIPTION |
|------|-------------|
| 1    | base        |
| 2, 4 | collector   |
| 3    | emitter     |



### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

| SYMBOL           | PARAMETER                     | CONDITIONS                       | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V <sub>CB0</sub> | collector-base voltage        | open emitter                     | –    | 75   | V    |
| V <sub>CEO</sub> | collector-emitter voltage     | open base                        | –    | 40   | V    |
| V <sub>EBO</sub> | emitter-base voltage          | open collector                   | –    | 6    | V    |
| I <sub>C</sub>   | collector current (DC)        |                                  | –    | 600  | mA   |
| I <sub>CM</sub>  | peak collector current        |                                  | –    | 800  | mA   |
| I <sub>BM</sub>  | peak base current             |                                  | –    | 200  | mA   |
| P <sub>tot</sub> | total power dissipation       | T <sub>amb</sub> ≤ 25 °C; note 1 | –    | 1.15 | W    |
| T <sub>stg</sub> | storage temperature           |                                  | –65  | +150 | °C   |
| T <sub>j</sub>   | junction temperature          |                                  | –    | 150  | °C   |
| T <sub>amb</sub> | operating ambient temperature |                                  | –65  | +150 | °C   |

### Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see “Thermal considerations for SOT223 in the General Part of associated Handbook”.

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## THERMAL CHARACTERISTICS

| SYMBOL        | PARAMETER   | CONDITIONS | VALUE | UNIT |
|---------------|---|------------|-------|------|
| $R_{th\ j-a}$ | thermal resistance from junction to ambient         | note 1     | 109   | K/W  |
| $R_{th\ j-s}$ | thermal resistance from junction to soldering point |            | 28    | K/W  |

## Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>. For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

## CHARACTERISTICS

$T_j = 25\text{ °C}$  unless otherwise specified.

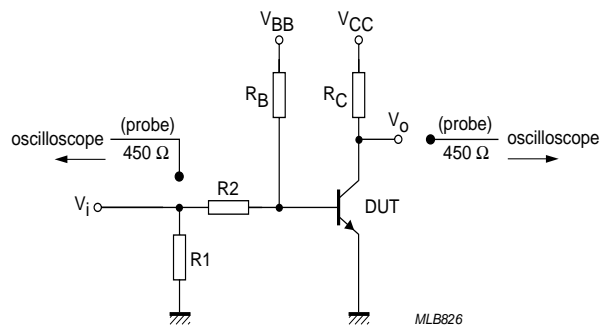
| SYMBOL   | PARAMETER                            | CONDITIONS  | MIN. | MAX. | UNIT          |
|--|--------------------------------------|---|------|------|---------------|
| $I_{CBO}$  | collector cut-off current            | $I_E = 0; V_{CB} = 60\text{ V}$   | –    | 10   | nA            |
|  |                                      | $I_E = 0; V_{CB} = 60\text{ V}; T_{amb} = 125\text{ °C}$  | –    | 10   | $\mu\text{A}$ |
| $I_{EBO}$  | emitter cut-off current              | $I_C = 0; V_{EB} = 5\text{ V}$  | –    | 10   | nA            |
| $h_{FE}$   | DC current gain                      | $I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$   | 35   | –    |               |
|  |                                      | $I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$   | 50   | –    |               |
|  |                                      | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$  | 75   | –    |               |
|  |                                      | $I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$                                 | 35   | –    |               |
|  |                                      | $I_C = 150\text{ mA}; V_{CE} = 1\text{ V}; \text{note 1}$   | 50   | –    |               |
|  |                                      | $I_C = 150\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$  | 100  | 300  |               |
|  |                                      | $I_C = 500\text{ mA}; V_{CE} = 10\text{ V}; \text{note 1}$  | 40   | –    |               |
| $V_{CEsat}$  | collector-emitter saturation voltage | $I_C = 150\text{ mA}; I_B = 15\text{ mA}$   | –    | 300  | mV            |
|  |                                      | $I_C = 500\text{ mA}; I_B = 50\text{ mA}$   | –    | 1    | V             |
| $V_{BEsat}$  | base-emitter saturation voltage      | $I_C = 150\text{ mA}; I_B = 15\text{ mA}$   | 0.6  | 1.2  | V             |
|  |                                      | $I_C = 500\text{ mA}; I_B = 50\text{ mA}$   | –    | 2    | V             |
| $C_c$  | collector capacitance                | $I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$   | –    | 8    | pF            |
| $C_e$  | emitter capacitance                  | $I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$   | –    | 25   | pF            |
| $f_T$  | transition frequency                 | $I_C = 20\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$                                      | 300  | –    | MHz           |
| <b>Switching times (between 10% and 90% levels); (see Fig.2)</b> |                                      |   |      |      |               |
| $t_{on}$   | turn-on time                         | $I_{Con} = 150\text{ mA}; I_{Bon} = 15\text{ mA}; I_{Boff} = -15\text{ mA}; T_{amb} = 25\text{ °C}$ | –    | 35   | ns            |
| $t_d$  | delay time                           |   | –    | 10   | ns            |
| $t_r$  | rise time                            |   | –    | 25   | ns            |
| $t_{off}$  | turn-off time                        |   | –    | 250  | ns            |
| $t_s$  | storage time                         |   | –    | 200  | ns            |
| $t_f$  | fall time                            |   | –    | 60   | ns            |

## Note

1. Pulse test:  $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$ .

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$V_i = 9.5 \text{ V}$ ;  $T = 500 \text{ } \mu\text{s}$ ;  $t_p = 10 \text{ } \mu\text{s}$ ;  $t_r = t_f \leq 3 \text{ ns}$ .  
 $R_1 = 68 \text{ } \Omega$ ;  $R_2 = 325 \text{ } \Omega$ ;  $R_B = 325 \text{ } \Omega$ ;  $R_C = 160 \text{ } \Omega$ .  
 $V_{BB} = -3.5 \text{ V}$ ;  $V_{CC} = 29.5 \text{ V}$ .  
 Oscilloscope input impedance  $Z_i = 50 \text{ } \Omega$ .

Fig.2 Test circuit for switching times.

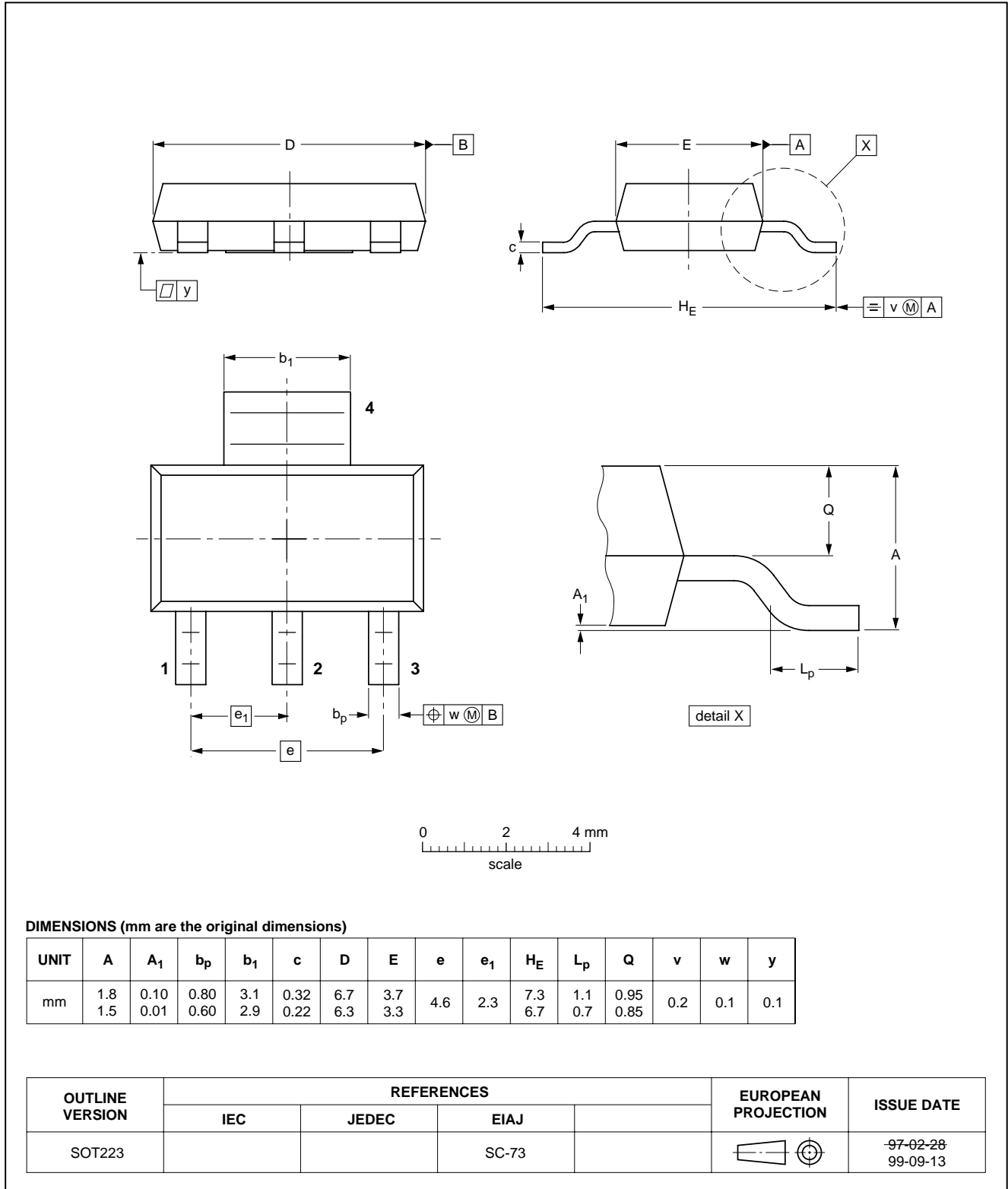
NPN switching transistor

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PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



## NPN switching transistor

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## DATA SHEET STATUS

| DOCUMENT STATUS <sup>(1)</sup> | PRODUCT STATUS <sup>(2)</sup> | DEFINITION  |
|--------------------------------|-------------------------------|---|
| Objective data sheet           | Development                   | This document contains data from the objective specification for product development. |
| Preliminary data sheet         | Qualification                 | This document contains data from the preliminary specification.                       |
| Product data sheet             | Production                    | This document contains the product specification.                                     |

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